TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS -H)

# **TPCC8005-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 9.1 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS (ON)} = 5.2 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 4.5 \text{ V})$ 

- High forward transfer admittance: |Yfs| = 79 S (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode:  $V_{th} = 1.3$  to 2.3 V ( $V_{DS} = 10$  V,  $I_D = 0.5$  mA)

### Absolute Maximum Ratings (Ta = 25°C)

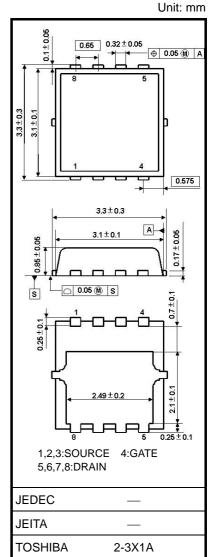
Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	30	V	
Drain-gate voltage (R	$GS = 20 \text{ k}\Omega$	$V_{DGR}$	30	V	
Gate-source voltage		$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub> 26		Α	
Diam current	Pulsed (Note 1)	$I_{DP}$	78	Α	
Drain power dissipation	on (Tc = 25 )	$P_{D}$	30 W		
Drain power dissipation	on $(t = 10 s)$ (Note 2a)	P <sub>D</sub>	1.9	W	
Drain power dissipation	on (t = 10 s) (Note 2b)	P <sub>D</sub>	0.7	W	
Single-pulse avalanch	ne energy (Note 3)	E <sub>AS</sub>	176	mJ	
Avalanche current		I <sub>AR</sub>	26	Α	
Repetitive avalanche	energy c = 25 ) (Note 4)	E <sub>AR</sub>	2.74	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and

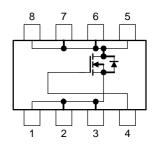
Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.02 g (typ.)

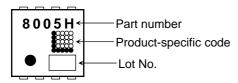
### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25 )	R <sub>th (ch-c)</sub>	4.2	°C/W
Thermal resistance, channel to ambient $(t = 10 \text{ s})$ (Note 2a)	R <sub>th (ch-a)</sub>	66	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	180	°C/W

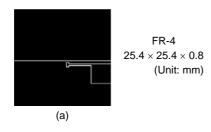
## Marking (Note 5)

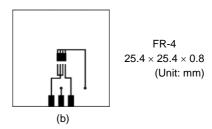


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

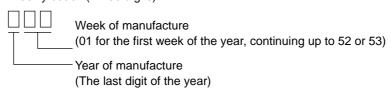




Note 3:  $V_{DD} = 24~V,~T_{Ch} = 25^{\circ}C$  (initial),  $L = 200~\mu H,~R_G = 25~\Omega,~I_{AR} = 26~A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



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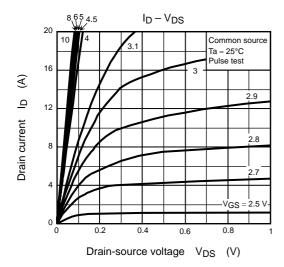
# Electrical Characteristics (Ta = 25°C)

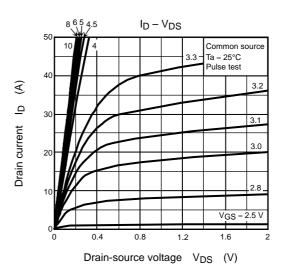
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V		_	10	μА
Droin course bro	akdawa valtaga	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	- + ±100 - 10 30 10 15 13 - 5.2 7.4 - 4.3 6.4 40 79 - 2200 2900 - 140 220 - 440 - 3.4 5.1 - 4.5 12 12 9.8 - 52 35 19 19	- V	
Drain-source breakdown voltage		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_		_
Gate threshold vo	oltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_{D} = 0.5 \text{ mA}$	1.3	_	2.3	V
Drain-source ON	Drain-source ON-resistance		$V_{GS} = 4.5 \text{ V}, I_D = 13 \text{ A}$	_	5.2	7.4	mO
Dialii-source ON	-resistance	NDS (ON)	$V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$	_	4.3	6.4	mΩ
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 13 A	40	79	_	S
Input capacitance	9	C <sub>iss</sub>		_	2200	2900	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	140	220	pF
Output capacitance		C <sub>oss</sub>		_	440	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 5 \text{ MHz}$	_	3.4	5.1	Ω
	Rise time	t <sub>r</sub>	10 V □ In = 13 A	_	4.5	_	
Cuitabina tima	Turn-on time	$\begin{array}{c} V_{\text{(BR) DSS}} & I_{D} = 10 \text{ mA}, V_{\text{GS}} = 0 \text{ V} \\ V_{\text{(BR) DSX}} & I_{D} = 10 \text{ mA}, V_{\text{GS}} = -20 \text{ V} \\ V_{\text{th}} & V_{\text{DS}} = 10 \text{ V}, I_{D} = 0.5 \text{ mA} \\ V_{\text{GS}} = 10 \text{ V}, I_{D} = 0.5 \text{ mA} \\ V_{\text{GS}} = 10 \text{ V}, I_{D} = 13 \text{ A} \\ V_{\text{GS}} = 10 \text{ V}, I_{D} = 13 \text{ A} \\ V_{\text{CS}} = 10 \text{ V}, I_{D} = 13 \text{ A} \\ V_{\text{DS}} = 10 \text{ V}, I_{D} = 13 \text{ A} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{CS}} = 0 \text{ V}, f = 5 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{CS}} = 0 \text{ V}, f = 5 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{CS}} = 0 \text{ V}, f = 5 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{CS}} = 0 \text{ V}, f = 5 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{DS}} = 10 \text{ V}, V_{\text{CS}} = 0 \text{ V}, f = 5 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{CS}} = 0 \text{ V}, f = 5 \text{ MHz} \\ V_{\text{DS}} = 10 \text{ V}, V_{\text{CS}} = 10 \text{ V}, V_{\text$	_				
Switching time	Fall time	t <sub>f</sub>	RL = 1.7.	_	9.8		ns
	Turn-off time	t <sub>off</sub>		_	52	_	
Total gate charge	•	0	V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 26 A		_		
(gate-source plus	gate-drain)	Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 26 \text{ A}$	_	19		
Gate-source charge 1		Q <sub>gs1</sub>	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 26 \text{ A}$	_	6.6	_	nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>		_	6.2	_	
Gate switch char	ge	Q <sub>SW</sub>		_	9.1	_	

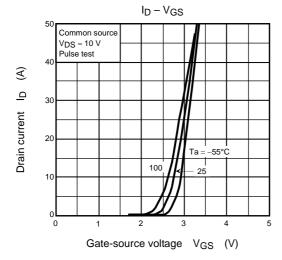
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

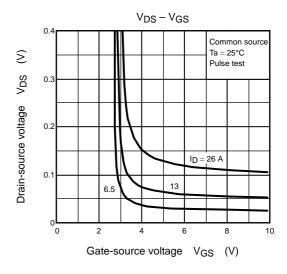
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	78	Α
Forward voltage (diode)			V <sub>DSF</sub>	$I_{DR} = 26 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.2	V

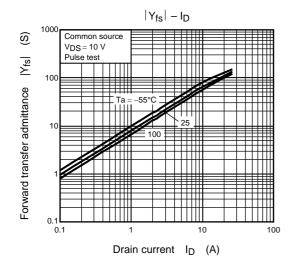
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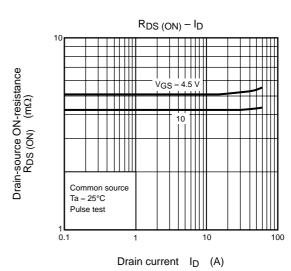




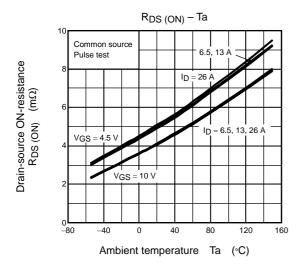


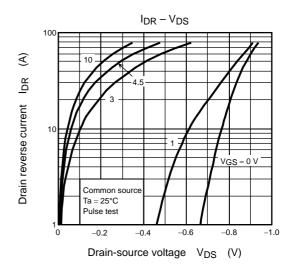


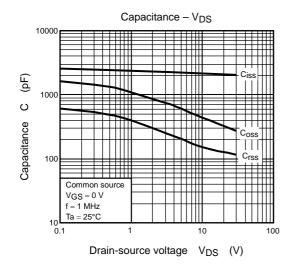


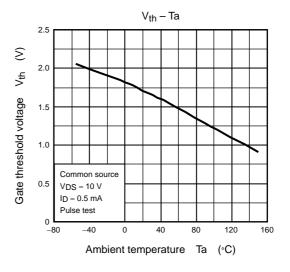


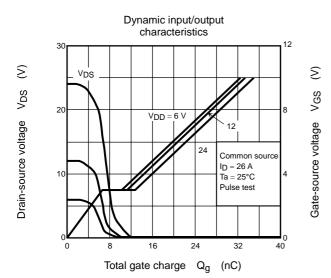
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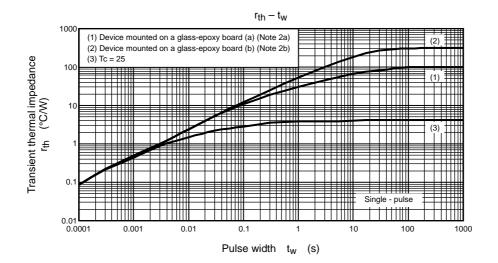


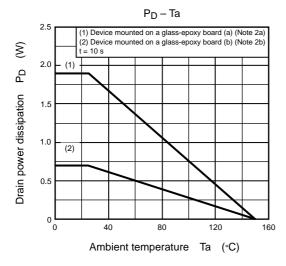


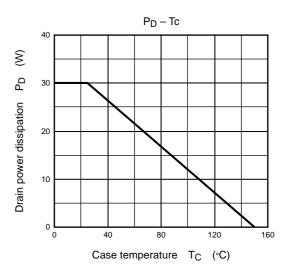


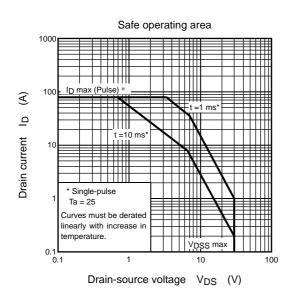


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